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TITLE: MANUFACTURING METHOD FOR SEMICONDUCTOR DEVICE

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INVENTOR-INFORMATION:

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ABSTRACT:

PROBLEM TO BE SOLVED: To provide a method of manufacturing a semiconductor device at high throughput.

SOLUTION: For adding a catalytic element for accelerating the crystallization of an amorphous Si film 102, an ion implanting method is utilized wherein the areas occupied by catalytic element-adding regions 107, 108 are reduced to increase the area of a crystal Si film available for TFTs, thereby increasing the degree of freedom of the circuit design. The step of crystallizing the Si film and gettering step for the catalytic element are conducted successively to greatly improve the throughput.

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